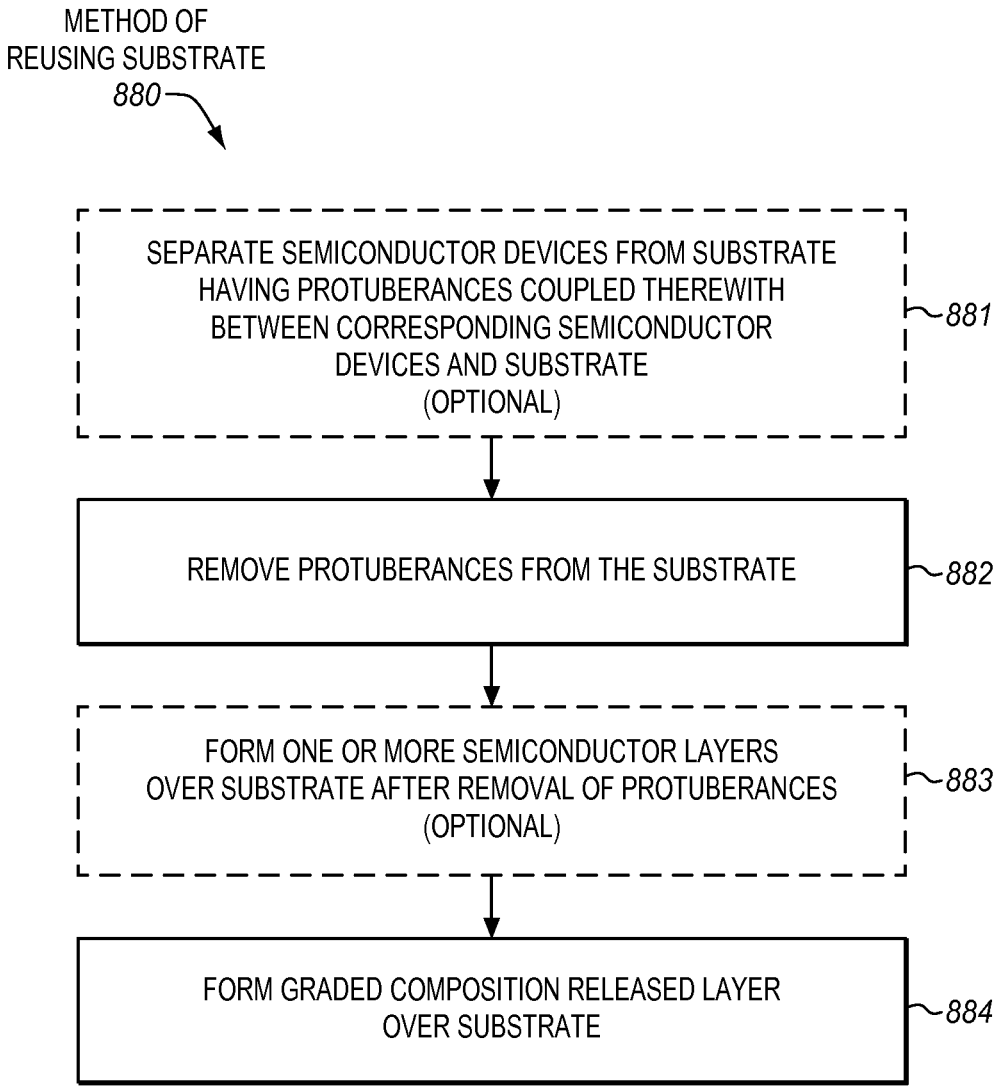
FIG. 8


METHOD OF
REUSING SUBSTRATE
880
SEPARATE SEMICONDUCTOR DEVICES FROM SUBSTRATE HAVING PROTUBERANCES COUPLED THEREWITH BETWEEN CORRESPONDING SEMICONDUCTOR DEVICES AND SUBSTRATE (OPTIONAL)
881
REMOVE PROTUBERANCES FROM THE SUBSTRATE
882
FORM ONE OR MORE SEMICONDUCTOR LAYERS OVER SUBSTRATE AFTER REMOVAL OF PROTUBERANCES (OPTIONAL)
883
FORM GRADED COMPOSITION RELEASED LAYER OVER SUBSTRATE
884